

PS8352AL2

ANALOG OUTPUT TYPE OPTICAL COUPLED ISOLATION AMPLIFIER

DESCRIPTION

The PS8352AL2 is an optically coupled isolation amplifier that uses an IC with a high-accuracy sigma-delta A/D converter and a GaAIAs light-emitting diode with high-speed response and high luminance efficiency on the input side, and an IC with a high-accuracy D/A converter on the output side.

The PS8352AL2 is designed specifically for high common mode transient immunity (CMTI) and high linearity (nonlinearity). The PS8352AL2 is designed for current and voltage sensing.

FEATURES

- Non-linearity (NL200 = 0.35% MAX.)
- High common mode transient immunity (CMTI = $10 \text{ kV}/\mu \text{s}$ MIN.)
- High isolation voltage (BV = 5 000 Vr.m.s.)
- Gain tolerance (G = 7.92 to 8.08 (±1%)) Gain: 8 V/V TYP.
- Package: 8-pin DIP lead bending type for long creepage distance for surface mount (L2)
- Embossed tape product: PS8352AL2-E3: 2 000 pcs/reel
- Pb-Free product
- Safety standards
 - UL approved: No. E72422
 - CSA approved: No. CA 101391 (CA5A, CAN/CSA-C22.2 60065, 60950)
 - DIN EN 60747-5-5 (VDE 0884-5) approved (Option)

APPLICATIONS

- AC Servo, inverter
- Solar power conditioner
- Measurement equipment



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PACKAGE DIMENSIONS (UNIT: mm)

Lead Bending Type (Gull-wing) For Long Creepage Distance For Surface Mount (L2)



Weight: 0.316g (typ.)

PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	8 mm
Outer Creepage Distance	8 mm
Isolation Distance	0.4 mm



MARKING EXAMPLE



ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number* ¹
PS8352AL2	PS8352AL2-AX	Pb-Free	Magazine case 50 pcs	Standard products	PS8352AL2
PS8352AL2-E3	PS8352AL2-E3-AX	(Ni/Pd/Au)	Embossed Tape 1 000 pcs/reel	(UL, CSA approved)	
PS8352AL2-V	PS8352AL2-V-AX		Magazine case 50 pcs	UL, CSA approved	
PS8352AL2-V-E3	PS8352AL2-V-E3-AX		Embossed Tape 1 000 pcs/reel	DIN EN 60747-5-5 (VDE 0884-5) 2011-11 approved (Option)	

*1 For the application of the Safety Standard, following part number should be used.



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Operating Ambient Temperature	TA	-40 to +110	С°
Storage Temperature	Tstg	-55 to+125	۵°
Supply Voltage	V_{DD1}, V_{DD2}	0 to 5.5	V
Input Voltage	VIN+, VIN-	–2 to V _{DD1} +0.5	V
2 Seconds Transient Input Voltage	VIN+, VIN-	-6 to V _{DD1} +0.5	V
Output Voltage	V_{OUT+}, V_{OUT-}	–0.5 to V _{DD2} +0.5	V
Isolation Voltage ^{*1}	BV	5 000	Vr.m.s.

*1 AC voltage for 1 minute at $T_A = 25^{\circ}$ C, RH = 60% between input and output. Pins 1-4 shorted together, 5-8 shorted together.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	MAX.	Unit
Operating Ambient Temperature	TA	-40	110	۵°
Supply Voltage	Vdd1, Vdd2	4.5	5.5	V
Input Voltage (Accurate and Linear) ^{*1}	V_{IN+}, V_{IN-}	-200	200	mV

*1 Using $V_{IN-} = 0$ V (to be connected to GND1) is recommended. Avoid using V_{IN-} of 2.5 V or more, because the internal test mode is activated when the voltage V_{IN-} reaches more than 2.5 V.



ELECTRICAL CHARACTERISTICS (DC Characteristics)

(TYP.: $T_A = 25^{\circ}C$, $V_{IN+} = V_{IN-} = 0$ V, $V_{DD1} = V_{DD2} = 5$ V, MIN., MAX.: refer to RECOMMENDED OPERATING CONDITIONS, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input Offset Voltage	Vos	T _A = 25°C	-2	-0.25	2	mV
			-3	-0.25	3	
Input Offset Voltage Drift	dVos/dT _A			1.6	10	μV/°C
vs. Temperature						
Gain ^{*1}	G	$-200~mV \leq V_{IN+} \leq 200~mV,$	7.92	8	8.08	V/V
		T _A = 25°C				
Gain Drift vs. Temperature	dG/dT _A			0.0006		V/V°C
Vout Non-linearity (200 mV) *2	NL200	$-200~mV \leq V_{IN+} \leq 200~mV$		0.014	0.35	%
VOUT Non-linearity (200 mV) Drift	dNL200/dT			0.0001		%/°C
vs. Temperature	А					
Vout Non-linearity (100 mV) *2	NL100	$-100~mV \leq V_{IN+} \leq 100~mV$		0.011	0.2	%
Maximum Input Voltage before	$ V_{IN+} MAX.$			320		mV
Vout Clipping						
Input Supply Current	IDD1	V _{IN+} = 400 mV		13.5	16	mA
Output Supply Current	I _{DD2}	V _{IN+} = -400 mV		7.8	16	mA
Input Bias Current	I _{IN+}	$V_{IN+} = 0V$	-1	-0.65	1	μA
Input Bias Current Drift	dI _{IN+} /dT _A			0.3		nA/°C
vs. Temperature						
Low Level Saturated Output	V _{OL}	V _{IN+} = -400 mV		1.29		V
Voltage						
High Level Saturated Output	Vон	V _{IN+} = 400 mV		3.8		V
Voltage						
Output Voltage ($V_{IN+} = V_{IN-} = 0 V$)	Vосм	$V_{IN+} = V_{IN-} = 0 V$	2.2	2.55	2.8	V
Output Short-circuit Current	losc			20		mA
Equivalent Input Resistance	RIN			450		kΩ
Vout Output Resistance	Rout			4		Ω
Input DC Common-Mode	CMRRIN			76		dB
Rejection Ratio ^{*3}						

- *1 The differential output voltage $(V_{0UT+} V_{0UT-})$ with respect to the differential input voltage $(V_{IN+} V_{IN-})$, where $V_{IN+} = -200 \text{ mV}$ to 200 mV and $V_{IN-} = 0 \text{ V}$) is measured under the circuit shown in **Fig. 2 NL200, G Test Circuit**. Upon the resulting chart, the gain is defined as the slope of the optimum line obtained by using the method of least squares.
- *2 The differential output voltage (V_{OUT+} V_{OUT-}) with respect to the differential input voltage (V_{IN+} V_{IN-}) is measured under the circuit shown in Fig. 2 NL200, G Test Circuit. Upon the resulting chart, the optimum line is obtained by using the method of least squares. Non-linearity is defined as the ratio (%) of the optimum line obtained by dividing [Half of the peak to peak value of the (residual) deviation] by [full-scale differential output voltage]. For example, if the differential output voltage is 3.2 V, and the peak to peak value of the (residual) deviation is 22.4 mV, while the input V_{IN+} is ±200 mV, the output non-linearity is obtained as follows: NL200 = 22.4/(2 × 3 200) = 0.35%
- *3 CMRR_{IN} is defined as the ratio of the differential signal gain (when the differential signal is applied between the input pins) to the common-mode signal gain (when both input pins are connected and the signal is applied). This value is indicated in dB.



ELECTRICAL CHARACTERISTICS (AC Characteristics)

(TYP.: $T_A = 25^{\circ}C$, $V_{IN+} = V_{IN-} = 0$ V, $V_{DD1} = V_{DD2} = 5$ V, MIN., MAX.: refer to RECOMMENDED OPERATING CONDITIONS, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{OUT} Bandwidth (-3 dB)	f _C	V_{IN+} = 200 mVp-p, sine wave	50	100		kHz
Vout Noise	Nout	$V_{IN+} = 0 V$		15.6		mVr.m.s.
VIN to VOUT Signal Delay (50 to 10%)	tPD10	V_{IN+} = 0 to 150 mV step		2.4	3.3	μS
V_{IN} to V_{OUT} Signal Delay (50 to 50%)	t _{PD50}			4.2	5.6	
V _{IN} to V _{OUT} Signal Delay (50 to 90%)	tPD90			6.1	9.9	
Vout Rise Time/Fall Time (10 to 90%)	tr/tf	V_{IN+} = 0 to 150 mV step		3.1	6.6	μS
Common Mode Transient Immunity ^{*1}	CMTI	V _{CM} = 0.5 kV, t _r = 20 ns,	10	28		kV/μs
		T _A = 25°C				
Power Supply Noise Rejection ^{*2}	PSR	f = 1 MHz		40		mVr.m.s.

*1 CMTI is tested by applying a pulse that rises and falls suddenly ($V_{CM} = 0.5 \text{ kV}$) between GND1 on the input side and GND2 on the output side (pins 4 and 5) by using the circuit shown in **Fig. 9 CMTI Test Circuit**. CMTI is defined at the point where the differential output voltage ($V_{OUT+} - V_{OUT-}$) fluctuates 200 mV (>1 μ s) or more from the average output voltage.

*2 This is the value of the transient voltage at the differential output when 1 V_{p-p}, 1 MHz, and 40 ns rise/fall time square wave is applied to both V_{DD}1 and V_{DD}2.



TEST CIRCUIT







TYPICAL CHARACTERISTICS (T_A = 25°C, unless otherwise specified)















Remark The graphs indicate nominal characteristics.



TAPING SPECIFICATIONS (UNIT: mm)





RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)





NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature
- Time of temperature higher than 220°C
- Time to preheat temperature from 120 to 180°C
- Number of reflows
- Flux

- 10 seconds or less
- 60 seconds or less
- 120±30 s

Three

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



Time (s)

(2) Wave soldering

Time

• Flux

Temperature 260°C or below (molten solder temperature)

- 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
 - Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Soldering by Soldering Iron

Peak Temperature (lead part temperature) 350°C or below
Time (each pins) 3 seconds or less
Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead



(4) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

USAGE CAUTIONS

- 1. Usage cautions
 - (1) This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
 - (2) When the primary power supply (VDD1) is off and only the secondary power supply (VDD2) is being applied (VDD1 = 0 V and VDD2 = 5 V), VOUT+ outputs a low level, and VOUT- outputs a high level (VOUT+ = 1.3 V TYP., VOUT- = 3.8 V TYP.), regardless of the input voltages (VIN+ and VIN-).
 - (3) The output level of VouT+ and VouT- might be unstable for several seconds immediately after the secondary power supply (VDD2) is applied while the primary power supply (VDD1) is being applied.
- 2. Board designing
 - (1) By-pass capacitor of more than 0.1 μ F is used between V_{cc} and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
 - (2) Keep the pattern connected the input (VIN+, VIN-) and the output (VOUT+, VOUT-), respectively, as short as possible.
 - (3) Do not connect any routing to the portion of the frame exposed between the pins on the package of the photocoupler. If connected, it will affect the photocoupler's internal voltage and the photocoupler will not operate normally.
 - (4) Because the maximum frequency of the signal input to the photocoupler must be lower than the allowable frequency band, be sure to connect an anti-aliasing filter (an RC filter with R = 68 Ω and C = 0.01 μ F, for example).
 - (5) The signals output from the PS8352A include noise elements such as chopping noise and quantization noise generated internally. Therefore, be sure to restrict the output frequency to the required bandwidth by adding a low-pass filter function (an RC filter with R =10 kΩ and C = 150 pF, for example) to the operational amplifier (post amplifier) in the next stage to the PS8352A.
- 3. Avoid storage at a high temperature and high humidity.



SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/110/21	
Dielectric strength maximum operating isolation voltage Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.5 \times U_{IORM}, P_d < 5 pC$	Uiorm Upr	1 130 1 695	V _{peak} V _{peak}
Test voltage (partial discharge test, procedure b for all devices) U_{pr} = 1.875 \times U_{IORM}, P_{d} < 5 pC	Upr	2 119	V _{peak}
Highest permissible overvoltage	Utr	8 000	Vpeak
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	CTI	175	
Material group (DIN EN 60664-1 VDE0110 Part 1)		III a	
Storage temperature range	Tstg	–55 to +125	°C
Operating temperature range	TA	-40 to +110	°C
Isolation resistance, minimum value $V_{IO} = 500 \text{ V dc at } T_A = 25^{\circ}\text{C}$ $V_{IO} = 500 \text{ V dc at } T_A MAX. at least 100^{\circ}\text{C}$	Ris MIN. Ris MIN.	10 ¹² 10 ¹¹	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current I _F , Psi = 0)	Tsi Isi	175 400	°C mA
Power (output or total power dissipation) Isolation resistance V _{IO} = 500 V dc at T _A = Tsi	Psi Ris MIN.	700 10 ⁹	mW

Dependence of maximum safety ratings with package temperature





V





 $t_{ini} = 60 \text{ sec}$





t₃,t₄ = 0.1 sec t_{m(PARTIAL DISCHARGE)}= 1.0 sec $t_{test} = 1.2 \text{ sec}$

Caution GaAs Products	This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.
	• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
	 Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
	Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
	Do not burn, destroy, cut, crush, or chemically dissolve the product.
	 Do not lick the product or in any way allow it to enter the mouth.



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